Icemos Technology Ltd **Product Specification** **1003.305001** Issue Date 08 November 2013 14

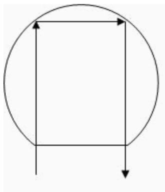
Part Number Customer

Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	[110]+/- 0.5°.	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none / semi standard	Wafer Vendor
	5.0	Secondary Flat Length	18.00 +/- 2.00 mm	Wafer Vendor
	6.0	Overall Thickness	1,003.00 +/- 5.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<15.00µm	ADE to ASTM F534, 20%
	9.0	Warp	<15.00µm	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
	12.0	Frontside final oxide thickness	27,000.00 +/- 1,500.00 A	Nanospec centre point, 4%
HandleSilicon	13.0	Backside Oxide thickness	27,000.00 +/- 1,500.00 A	Nanospec centre point, 4%
	14.0	Handle Growth Method	CZ	Wafer Vendor
	15.0	Handle Orientation	{100} +/- 0.5deg	Wafer Vendor
	16.0	Handle Thickness	1,000.00 +/- 5.00 µm	ADE, 100%
	17.0	Handle Doping Type	P/N	Wafer Vendor
	18.0	Handle Dopant		Wafer Vendor
	19.0	Handle Resistivity	>0.0001 Ohmcm	Wafer Vendor
	20.0	Backside Finish	Polished with lasermark	Nanospec centre point, 4%
	21.0	Total scratch length	Frontside = none. Backside = handing marks only.	Bright Light, 100% (note 2)
	22.0	Surface Haze	none	Bright Light, 100% (note 2)

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

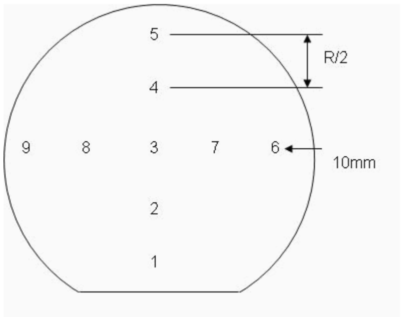
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information